

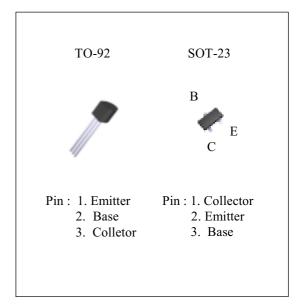
NPN Epitaxial Silicon Transistor

GENERAL PURPOSE TRANSISTOR

Collector-Emitter Voltage: V_{CEO} = 40V
 Collector Dissipation: P_{C (max)} = 625 mW

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Characteristics	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	$ m V_{CEO}$	40	V
Emitter-Base Voltage	$ m V_{EBO}$	6	V
Collector Current	I_{C}	200	mA
Collector Dissipation	P_{C}	625	mW
Junction Temperature	T_{j}	150	$^{\circ}$
Storage Temperature	T_{stg}	-55~150	$^{\circ}$



ELECTRICAL CHARACTERISTICS ($T_a = 25^{\circ}C$)

Characteristic	Symbol	Test Conditions	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage	$\mathrm{BV}_{\mathrm{CBO}}$	$I_{\rm C} = 10 \mu$ A , $I_{\rm E} = 0$	60			V
*Collector-Emitter Breakdown Voltage	$\mathrm{BV}_{\mathrm{CEO}}$	$I_C = 1 \text{mA}$, $I_B = 0$	40			V
Emitter-Base Breakdown Voltage	$\mathrm{BV}_{\mathrm{EBO}}$	$I_{E}=10 \mu A , I_{C}=0$	6			V
Collector Cut-off Curent	I_{CEX}	$V_{CE} = 30V, V_{BE} = 3V$			50	nA
Base Cut-off Current	$I_{ m BL}$	$V_{CE} = 30V, V_{BE} = 3V$			50	nA
*DC Current Gain	h_{FE}	$Ic = 0.1 \text{mA}, V_{CE} = 1 \text{V}$	40			
		$Ic = 1 \text{ mA}, V_{CE} = 1 \text{ V}$	70			
		$Ic=10mA; V_{CE}=1V$	100		300	
		$Ic = 50 \text{ mA}, V_{CE} = 1 \text{ V}$	60			
		$Ic = 100 \text{ mA}, V_{CE} = 1V$	30			
*Collector-Emitter Saturation Voltage	V _{CE(sat)}	$I_C = 10 \text{ mA}$, $I_B = 1 \text{mA}$			0.2	V
		$I_C = 50 \text{mA}$, $I_B = 5 \text{mA}$			0.3	V
*Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 10 \text{ mA}$, $I_B = 1 \text{mA}$	0.65		0.85	V
		$I_C = 50 \text{mA}$, $I_B = 5 \text{mA}$			0.95	V
Output Capacitance	C_{ob}	$V_{CB} = 5V, I_E = 0$			4	pF
	_	f=1MHz				
Current Gain Bandwidth Produce	$\mathbf{f}_{\mathtt{T}}$	$Ic = 10 \text{ mA}, V_{CE} = 20 \text{V}$	300			MHz
		f=100MHz				
Turn On Time	t _{on}	$Vcc = 3 V, V_{BE} = 0.5V$			70	ns
		$Ic = 10 \text{ mA}, I_{B1} = 1 \text{mA}$				
Turn Off Time	$t_{ m off}$	Vcc = 3V, $Ic = 1mA$			250	ns
		$I_{B1}=I_{B2}=1 \text{ mA}$				

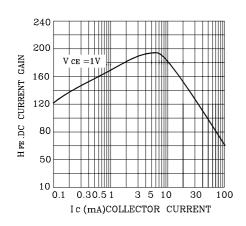
^{*}Pulse Test: Pulse Width $\leq 300~\mu$ s.Duty Cycle $\leq 2\%$

Classification	В	C	
$h_{ m FE}$	160-240	240-300	

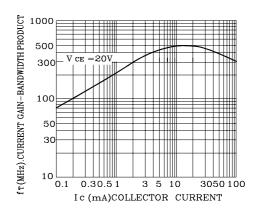


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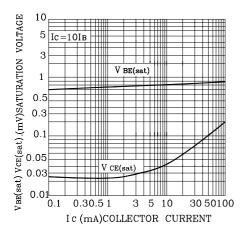
DC CURRENT GAIN



CURRENT GAIN-BANDWIDTH PRODUCT



BASE-EMITTER SATURATION VOLTAGE COLLECTOR-EMITTER SATURATION VOLTAGE



OUTPUT CAPACITANCE

